EMD4DXV6T1, EMD4DXV6T5

Preferred Devices

Dual Bias Resistor Transistors

NPN and PNP Silicon Surface Mount Transistors with Monolithic Bias Resistor Network

The BRT (Bias Resistor Transistor) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base−emitter resistor. These digital transistors are designed to replace a single device and its external resistor bias network. The BRT eliminates these individual components by integrating them into a single device. In the EMD4DXV6T1 series, two complementary BRT devices are housed in the SOT−563 package which is ideal for low power surface mount applications where board space is at a premium.

Features

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- These are Pb−Free Devices

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted, common for Q_1 and Q_2, − minus sign for Q_1 (PNP) omitted)

Rating	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	50	Vdc
Collector-Emitter Voltage	V_{CEO}	50	Vdc
Collector Current	I_C	100	mAdc

THERMAL CHARACTERISTICS

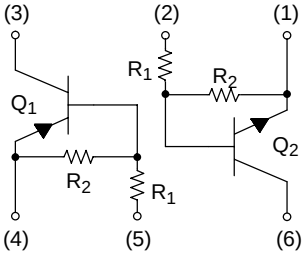
Characteristic (One Junction Heated)	Symbol	Max	Unit
Total Device Dissipation T_A = 25°C (Note 1) Derate above 25°C (Note 1)	P_D	357 2.9	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	350	°C/W
Total Device Dissipation T_A = 25°C (Note 1) Derate above 25°C	P_D	500 4.0	mW mW/°C
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	250	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

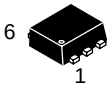
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

1. FR−4 board with minimum mounting pad.

ON Semiconductor®

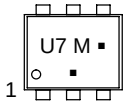
http://onsemi.com





SOT−563
CASE 463A
STYLE 1

MARKING DIAGRAM



U7 = Specific Device Code
M = Date Code
▪ = Pb−Free Package
(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
EMD4DXV6T1G	SOT−563 (Pb−Free)	4000/Tape & Reel
EMD4DXV6T5G	SOT−563 (Pb−Free)	8000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Q1 TRANSISTOR: PNP					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	−	−	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)	I_{CEO}	−	−	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_C = 5.0 mA)	I_{EBO}	−	−	0.2	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	−	−	Vdc
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	−	−	Vdc
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	h_{FE}	80	140	−	
Collector−Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(SAT)}$	−	−	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 2.5 V, R_L = 1.0 kΩ)	V_{OL}	−	−	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)	V_{OH}	4.9	−	−	Vdc
Input Resistor	R1	7.0	10	13	kΩ
Resistor Ratio	R1/R2	0.17	0.21	0.25	
Q2 TRANSISTOR: NPN					
OFF CHARACTERISTICS					
Collector-Base Cutoff Current (V_{CB} = 50 V, I_E = 0)	I_{CBO}	−	−	100	nAdc
Collector-Emitter Cutoff Current (V_{CB} = 50 V, I_B = 0)	I_{CEO}	−	−	500	nAdc
Emitter-Base Cutoff Current (V_{EB} = 6.0, I_C = 0 mA)	I_{EBO}	−	−	0.1	mAdc
ON CHARACTERISTICS					
Collector-Base Breakdown Voltage (I_C = 10 μA, I_E = 0)	$V_{(BR)CBO}$	50	−	−	Vdc
Collector-Emitter Breakdown Voltage (I_C = 2.0 mA, I_B = 0)	$V_{(BR)CEO}$	50	−	−	Vdc
DC Current Gain (V_{CE} = 10 V, I_C = 5.0 mA)	h_{FE}	80	140	−	
Collector−Emitter Saturation Voltage (I_C = 10 mA, I_B = 0.3 mA)	$V_{CE(SAT)}$	−	−	0.25	Vdc
Output Voltage (on) (V_{CC} = 5.0 V, V_B = 3.5 V, R_L = 1.0 kΩ)	V_{OL}	−	−	0.2	Vdc
Output Voltage (off) (V_{CC} = 5.0 V, V_B = 0.5 V, R_L = 1.0 kΩ)	V_{OH}	4.9	−	−	Vdc
Input Resistor	R1	32.9	47	61.1	kΩ
Resistor Ratio	R1/R2	0.8	1.0	1.2	

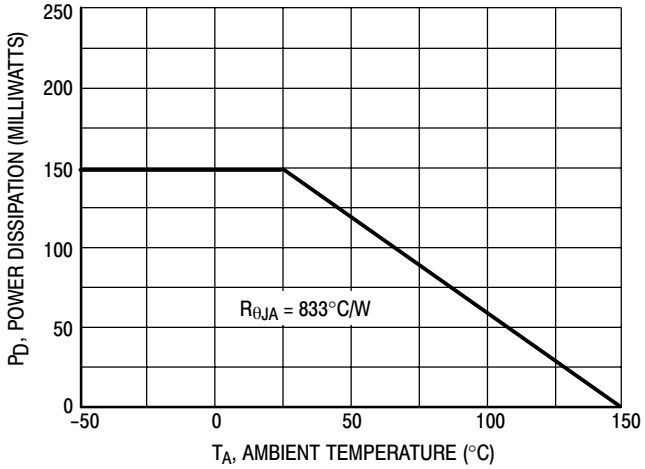


Figure 1. Derating Curve

TYPICAL ELECTRICAL CHARACTERISTICS — EMD4DXV6T1 PNP TRANSISTOR

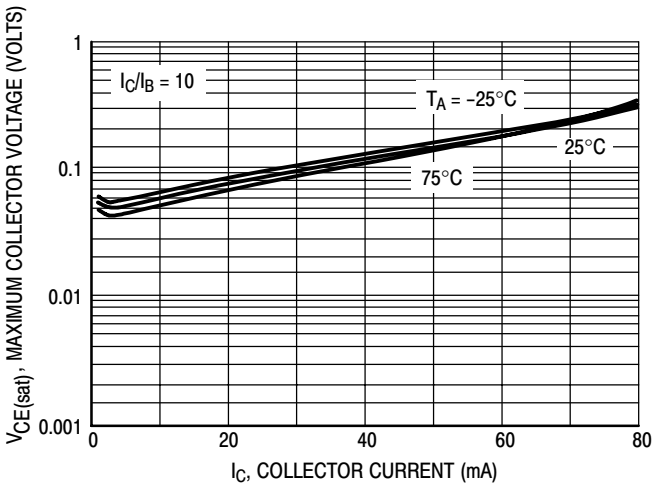


Figure 2. $V_{CE(sat)}$ versus I_C

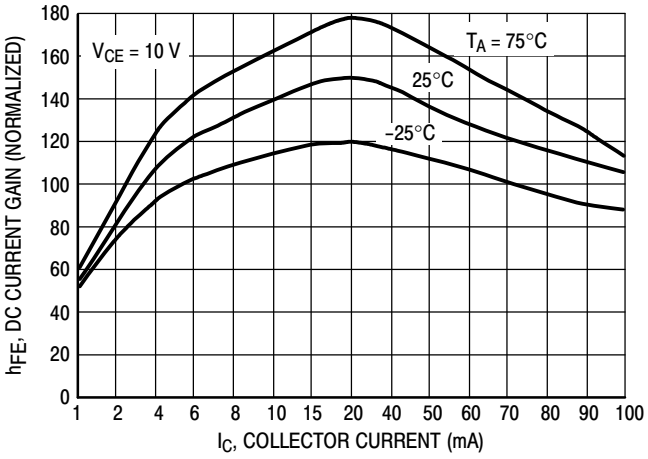


Figure 3. DC Current Gain

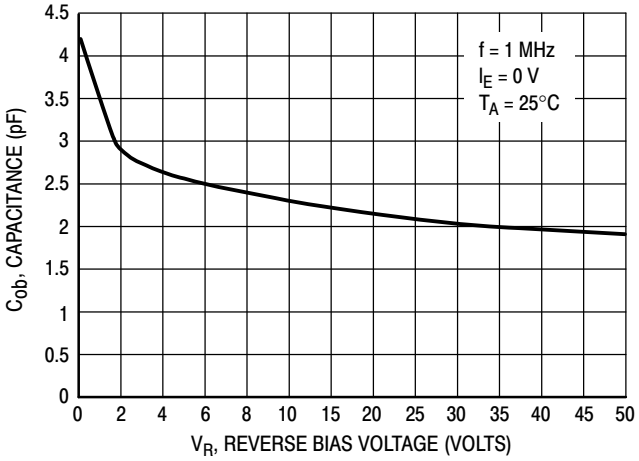


Figure 4. Output Capacitance

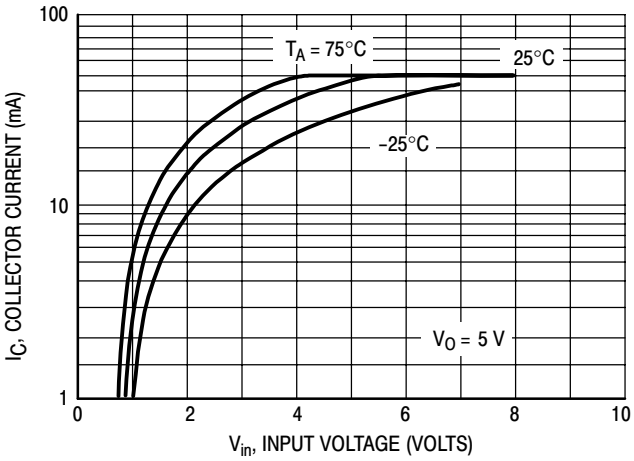


Figure 5. Output Current versus Input Voltage

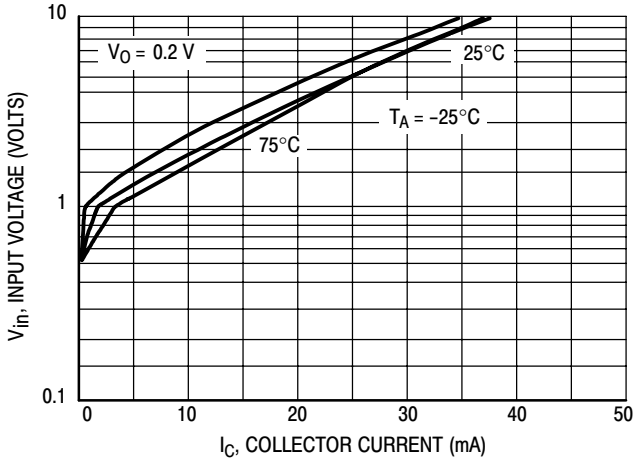


Figure 6. Input Voltage versus Output Current

TYPICAL ELECTRICAL CHARACTERISTICS — EMD4DXV6T1 NPN TRANSISTOR

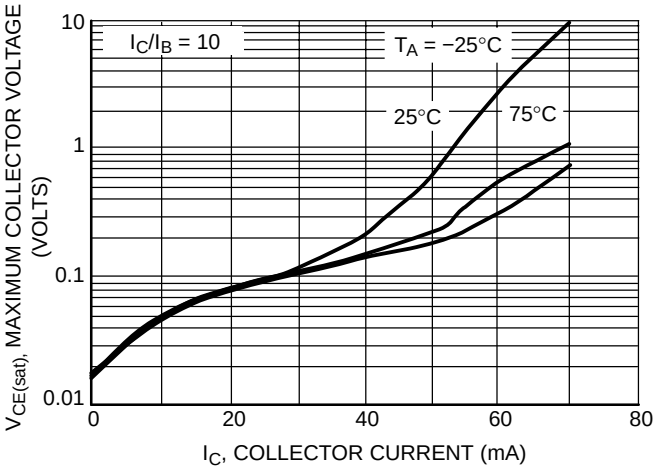


Figure 7. $V_{CE(sat)}$ vs. I_C

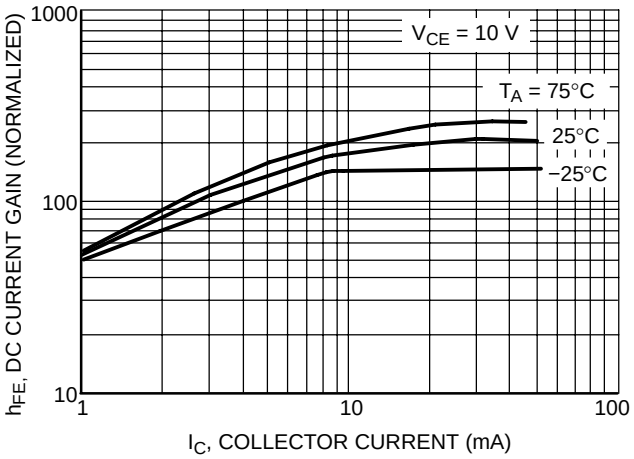


Figure 8. DC Current Gain

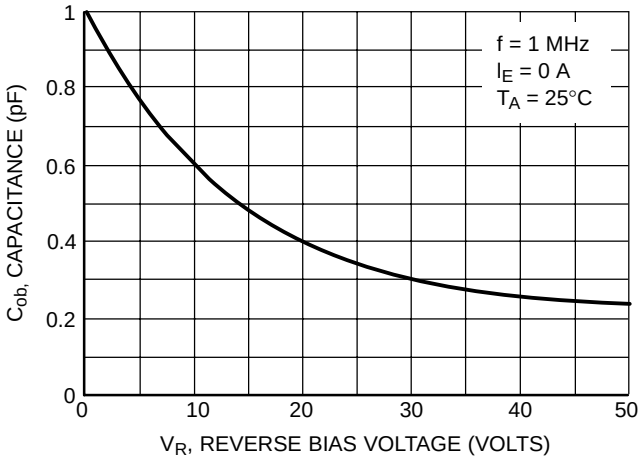


Figure 9. Output Capacitance

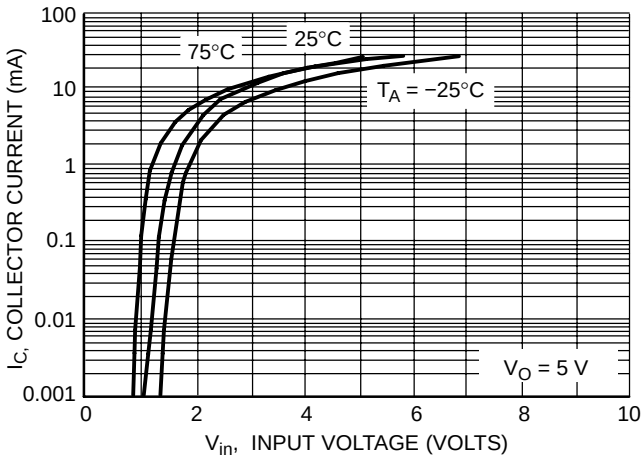


Figure 10. Output Current vs. Input Voltage

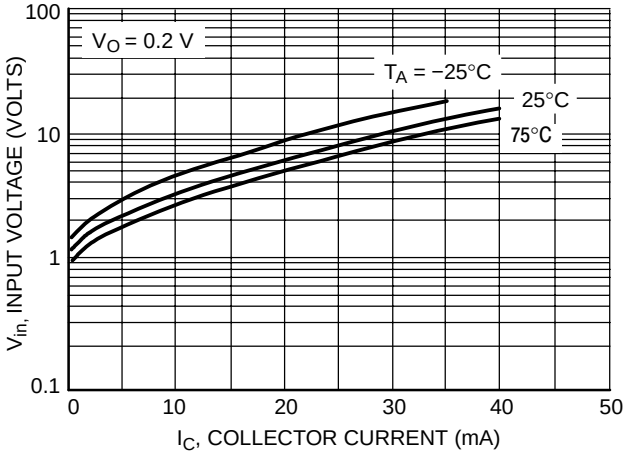
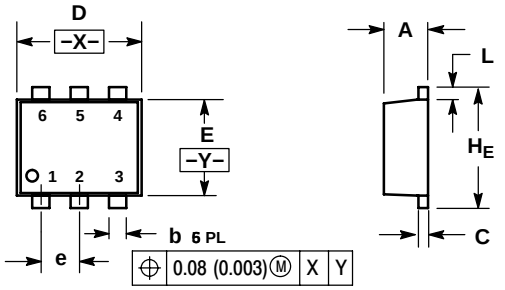


Figure 11. Input Voltage vs. Output Current

PACKAGE DIMENSIONS

SOT−563, 6 LEAD
CASE 463A−01
ISSUE F

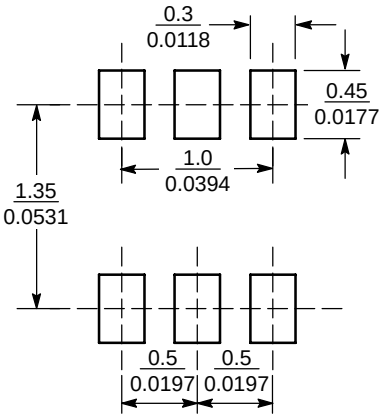


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	0.50	0.55	0.60	0.020	0.021	0.023
b	0.17	0.22	0.27	0.007	0.009	0.011
C	0.08	0.12	0.18	0.003	0.005	0.007
D	1.50	1.60	1.70	0.059	0.062	0.066
E	1.10	1.20	1.30	0.043	0.047	0.051
e	0.5 BSC			0.02 BSC		
L	0.10	0.20	0.30	0.004	0.008	0.012
H_E	1.50	1.60	1.70	0.059	0.062	0.066

STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1

SOLDERING FOOTPRINT*



SCALE 20:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

EMD4DXV6/D